

Sensors



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TLE4923

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Dynamic Differential Hall Effect Sensor IC

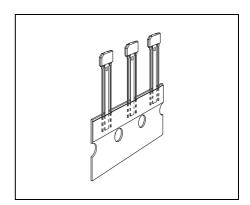
TLE4923

Bipolar IC

1 Overview

1.1 Features

- Advanced performance
- Higher sensitivity
- Symmetrical thresholds
- High piezo resistivity
- Reduced power consumption
- South and north pole pre-induction possible
- AC coupled
- Digital output signal
- Two-wire interface
- Large temperature range
- Large airgap
- Low cut-off frequency
- Protection against reversed polarity



The differential Hall effect sensor TLE4923 is compatible to the TLE4921-3U, except for having a 2-wire interface. The TLE4923 provides high sensitivity, a superior stability over temperature and symmetrical thresholds in order to achieve a stable duty cycle. TLE4923 is particularly suitable for rotational speed detection and timing applications of ferromagnetic toothed wheels such as in anti-lock braking systems, transmissions, crankshafts, etc. The integrated circuit (based on Hall effect) provides a digital signal output with frequency proportional to the speed of rotation. Unlike other rotational sensors differential Hall ICs are not influenced by radial vibration within the effective airgap of the sensor and require no external signal processing.

Туре	Marking	Ordering Code	Package
TLE4923	4923 B	Q62705-K408	PG-SSO-3-6



Overview

1.2 Pin Configuration

(top view)

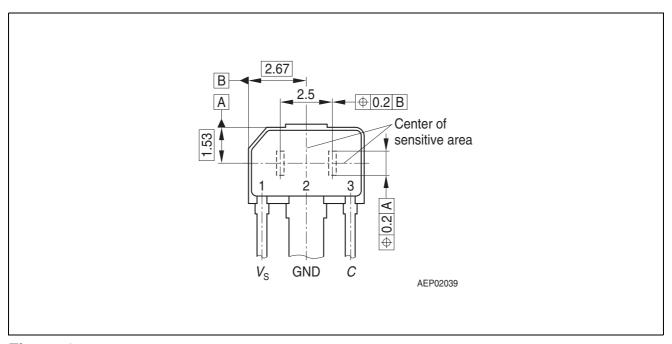


Figure 1

Table 1 Pin Definitions and Functions

Pin No.	Symbol	Function
1	V_{S}	Supply voltage
2	GND	Ground
3	C	Capacitor



General

2 General

2.1 Block Diagram

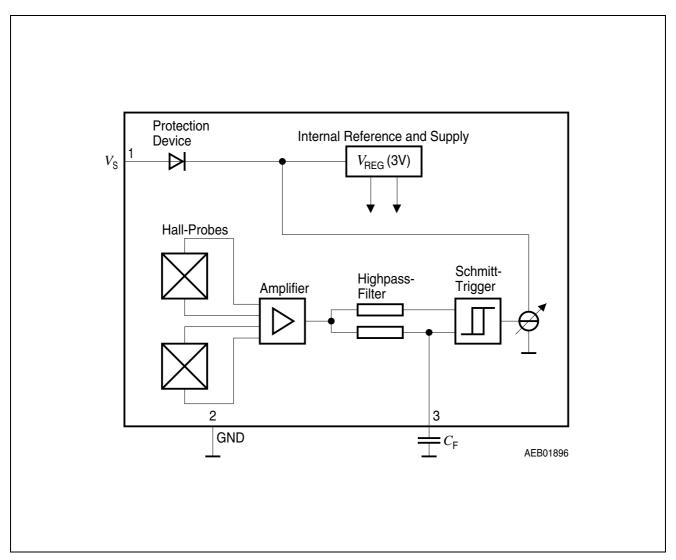


Figure 2 Block Diagram



General

2.2 Functional Description

The Differential Hall sensor IC detects the motion and position of ferromagnetic and permanent magnet structures by measuring the differential flux density of the magnetic field. To detect ferromagnetic objects the magnetic field must be provided by a back biasing permanent magnet (**south or north** pole of the magnet attached to the rear unmarked side of the IC package).

Using an external capacitor the generated Hall voltage signal is slowly adjusted via an active high pass filter with low frequency cut-off. This causes the output to switch into a biased mode after a time constant is elapsed. The time constant is determined by the external capacitor. Filtering avoids aging and temperature influence from Schmitt-trigger input and eliminates device and magnetic offset.

The TLE4923 can be exploited to detect toothed wheel rotation in a rough environment. Jolts against the toothed wheel and ripple have no influence on the output signal.

The on and off state of the IC are indicated by high and low current consumption.

2.3 Circuit Description (see Figure 2)

The TLE4923 is comprised of a supply voltage reference, a pair of Hall probes spaced at 2.5 mm, differential amplifier, filter for offset compensation, Schmitt-trigger, and a switched current source.

The TLE4923 was designed to have a wide range of application parameter variations. Differential fields up to ±40 mT can be detected without influence to the switching performance. The pre-induction field can either come from a magnetic south or north pole, whereby the field strength up to 500 mT or more will not influence the switching points¹⁾. The improved temperature compensation enables a superior sensitivity and accuracy over the temperature range. Finally, the optimized piezo compensation and the integrated dynamic offset compensation enable easy manufacturing and elimination of magnet offsets.

Protection is provided at the input/supply (pin 1) for reverse polarity.

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¹⁾ Differential bias fields exceeding ±20 mT, e. g. caused by a misaligned magnet, should be avoided.



Maximum Ratings

3 Maximum Ratings

Table 2 Absolute Maximum Ratings

Parameter	Symbol	Lin	nit Values	Unit	Remarks	
		min.	max.			
Supply voltage	V_{S}	-18 ¹⁾	24	V		
Capacitor voltage	V_{C}	-0.3	3	V		
Junction temperature	T_{j}	- - -	150 160 170 190	°C	5000 h 2500 h 500 h 4 h	
Storage temperature	T_{S}	-40	150	°C		
Thermal resistance	R_{thJA}	_	190	K/W	2)	

¹⁾ Reverse current drawn by the device < 10 mA

Note: Stresses above those listed here may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

²⁾ Can be reduced significantly by further packaging process, e. g. overmolding. The device is ESD protected up to 2 kV (HL test procedure)



Operating Range

4 Operating Range

Table 3 Operating Range

Parameter	Symbol	Limit Values			Unit	Conditions	
		min.	typ.	max.			
Supply voltage	V_{S}	4.5	_	18	V		
Junction temperature	T_{j}	-40 - - -	_ _ _ _	150 160 170 190	°C	5000 h 2500 h 500 h 4 h	
Pre-induction	B_0	-500	_	500	mT	At Hall probe; independent of magnet orientation	
Differential induction	ΔB	-40	_	40	mT		

Note: Unless otherwise noted, all temperatures refer to junction temperature. In the operating range the functions given in the circuit description are fulfilled.



5 Electrical Parameters

Table 4 Electrical Characteristics

The device characteristics listed below are guaranteed in the full operating range.

Parameter	Symbol	Limit Values			Unit	Test	Test
		min.	typ.	max.		Condition	Circuit
Supply current	I_{S}	3.1 8.1	4.1 10.5	5.3 13.6	mA mA		1
Supply current difference	I_{SON} - I_{SOFF}	5.0	6.4	8.3	mA		1
Supply current ratio	$I_{\rm SON}$ / $I_{\rm SOFF}$	2	2.4	3			1
Center of switching points: $(\Delta B_{\rm OP} + \Delta B_{\rm RP}) / 2$	ΔB_{m}	-0.5	0	0.5	mT	$\Delta B = 2.0 \text{ mT},$ f = 200 Hz, $-40^{\circ}\text{C} < T_{\text{j}} \le 150^{\circ}\text{C}^{-1)}$	2
Center of switching points: $(\Delta B_{\rm OP} + \Delta B_{\rm RP}) / 2$	ΔB_{m}	-0.7	0	0.7	mT	$\Delta B = 2.0 \text{ mT},$ f = 200 Hz, $150^{\circ}\text{C} < T_{\text{j}}$ $< 190^{\circ}\text{C}$ 1) 2)	2
Hysteresis	ΔB_{H}	1	1.5	2.2	mT	$\Delta B = 2.0 \text{ mT},$ $f = 200 \text{ Hz}^{3)}$	2
Current rise time	t_{r}	_	_	0.5	μs		2
Current fall time	t_{f}	_	_	0.5	μs		2
Delay time 4)	t_{dop} t_{drp} t_{dop} - t_{drp}			25 10 15	μs μs μs	f = 10 kHz, ΔB = 5 mT	2
Filter input resistance	R_{C}	35	43	52	kΩ	25°C ±2°C	1
Filter sensitivity to ΔB	S_{C}		8.5		mV/ mT	25°C ±2°C	1
Filter bias voltage	V_{C}	1.6	2.0	2.4	V	$\Delta B = 0$	1
Frequency	f	5)		10000	Hz	$\Delta B = 5 \text{ mT}$	2



Table 4Electrical Characteristics (cont'd)

The device characteristics listed below are guaranteed in the full operating range.

Parameter	Symbol	Limit Values			Unit	Test	Test
		min.	typ.	max.		Condition	Circuit
Resistivity against mechanical stress (piezo) 6)	$\Delta B_{m} \ \Delta B_{H}$	-0.1 -0.1	-	0.1 0.1	mT mT	F = 2 N	2
Power supply rejection ratio (PSRR)	V_{PSRR}	10	_	_	V	$V_{\rm S}$ modulated with $V_{\rm PSRR}$, $f_{\rm PSRR}$ = 10 kHz, $t_{\rm r,fPSRR}$ = 1 $\mu {\rm s}$, ΔB = 0, only 1 transition may occur	2 7)

- 1) For ΔB values larger than ± 10 mT this value may exceed the limits as follows: $|\Delta B_{\rm m}| < |0.05 \times \Delta B|$
- 2) Leakage currents at pin 3 should be avoided. The bias shift of $B_{\rm m}$ caused by a leakage current $I_{\rm L}$ can be calculated by: $\Delta B_{\rm m} = \frac{I_{\rm L} \times R_{\rm C}({\sf T})}{S_{\rm C}({\sf T})}$. See also the typical curves on Page 22.
- 3) Differential pre-induction (e.g. by magnetic misalignment) has to be smaller than 20 mT.
- 4) For definition see Figure 6.
- 5) Depends on filter capacitor $C_{\rm F}$. The cut-off frequency is given as $f = \frac{1}{2 \times \pi \times R_{\rm C} \times C_{\rm F}}$. The switching points are guaranteed over the whole frequency range, but amplitude modification and phase shift have to be taken into account due to the 1st order highpass filter.
- 6) For definition see Figure 7.
- 7) For definition see Figure 5.

Note: The listed characteristics are ensured over the operating range of the integrated circuit. Typical characteristics specify mean values expected over the production spread. If not otherwise specified, typical characteristics apply at $T_j = 25^{\circ}$ C and the given supply voltage.

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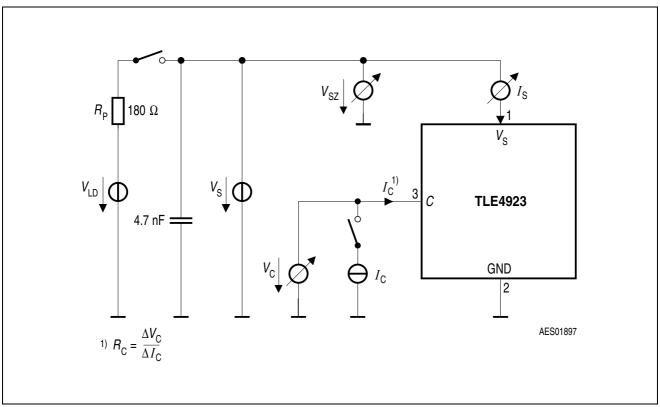


Figure 3 Test Circuit 1

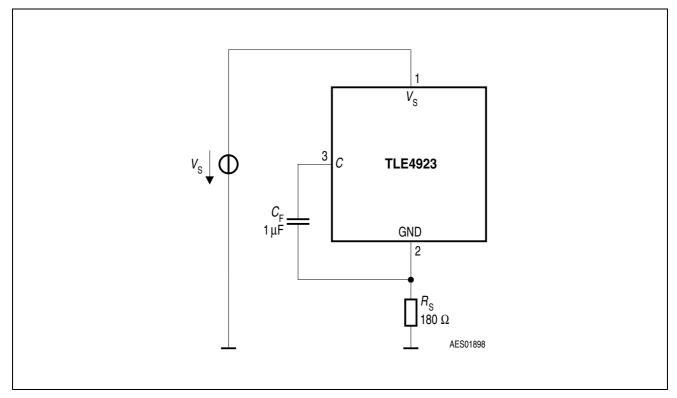


Figure 4 Test Circuit 2



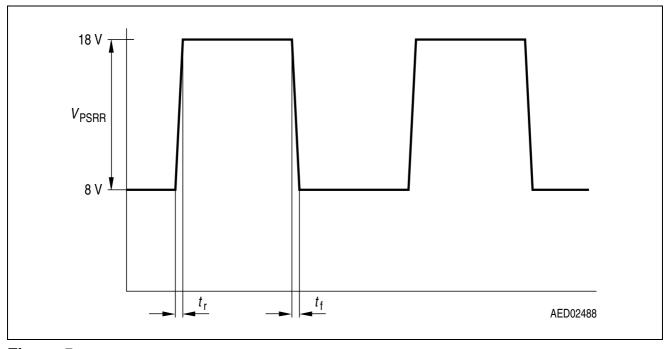


Figure 5

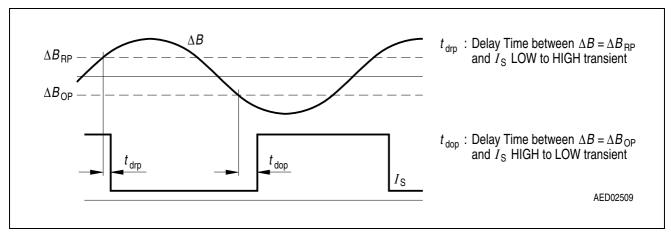


Figure 6 Definition of Delay Times (switching points related to initial measurement @ ΔB = 2 mT; f = 200 Hz)

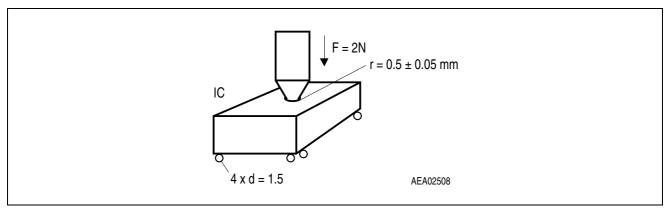


Figure 7 Setup for Piezo Measurements



6 Application Notes

Two possible applications are shown in **Figure 10** and **Figure 11** (Toothed and Magnet Wheel).

Two-wire application is shown in Figure 12.

Gear Tooth Sensing

In the case of ferromagnetic toothed wheel applications the IC has to be biased by the south or north pole of a permanent magnet (e.g. $SmCo_5$ (Vacuumschmelze VX170) with the dimensions 8 mm \times 5 mm \times 3 mm) which should cover both Hall probes.

The maximum air gap depends on:

- the magnetic field strength (magnet used; pre-induction) and
- the tooth wheel that is used (dimensions, material, etc.; resulting differential field).

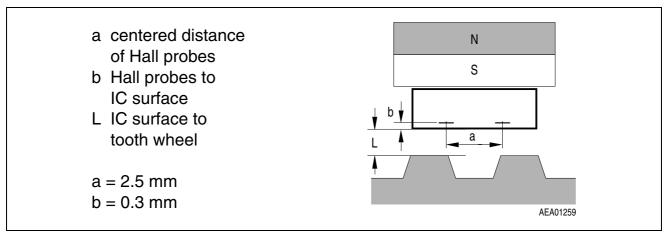


Figure 8 Sensor Spacing

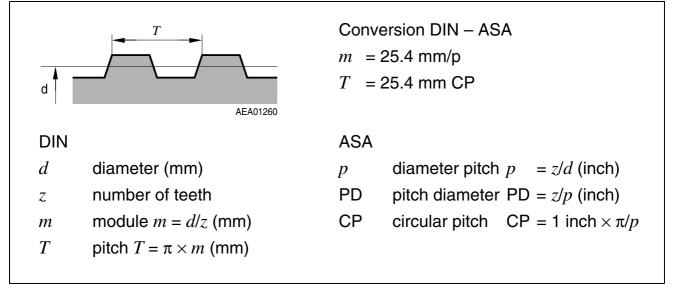


Figure 9 Tooth Wheel Dimensions



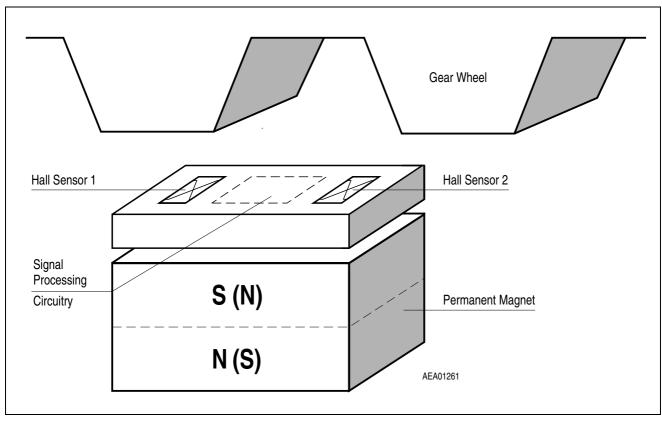


Figure 10 TLE4923, with Ferromagnetic Toothed Wheel

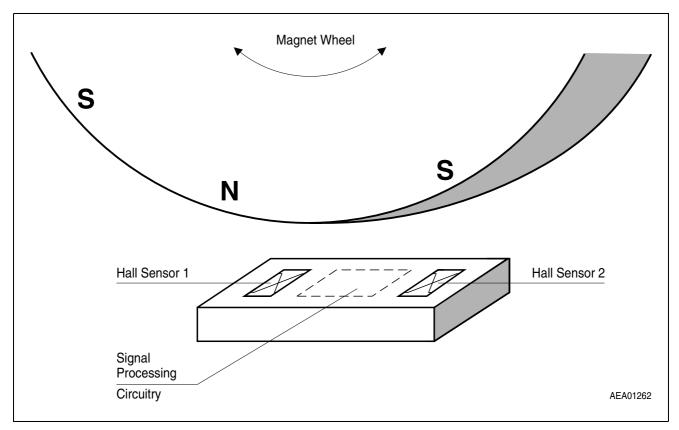


Figure 11 TLE4923, with Magnet Wheel



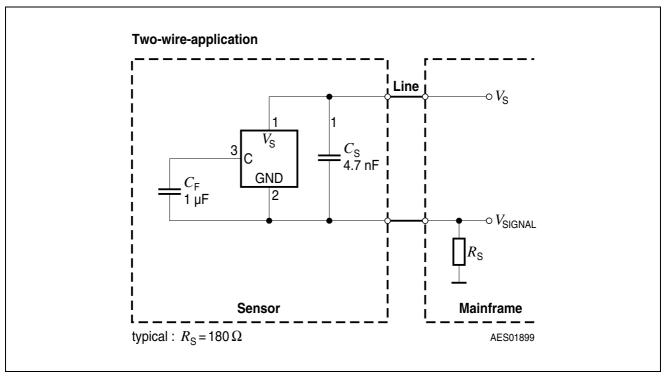


Figure 12 Application Circuit



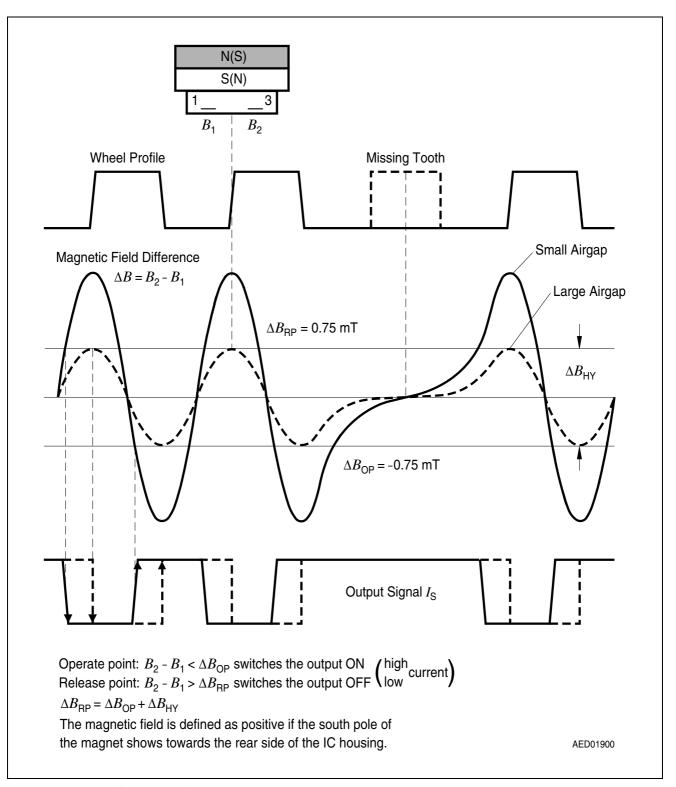


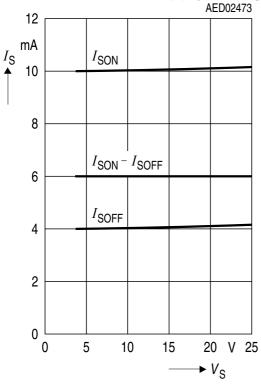
Figure 13 System Operation



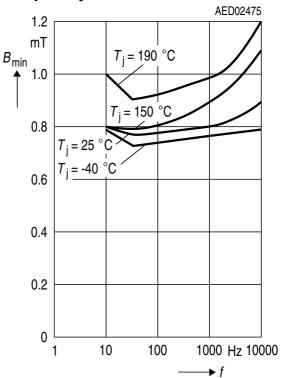
7 Typical Performance Characteristics

If not otherwise specified, all curves reflect typical values at $T_i = 25$ °C and $V_S = 12$ V.

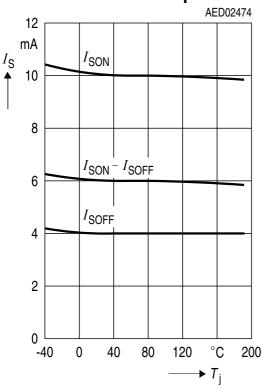
Supply Current and Supply Current Difference versus Supply Voltage



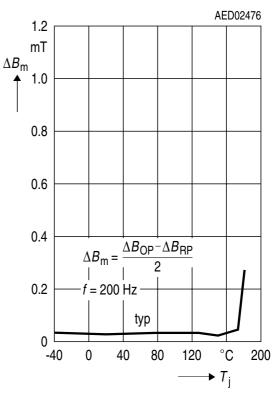
Minimum Switching Field versus Frequency



Supply Current and Supply Current Difference versus Temperature

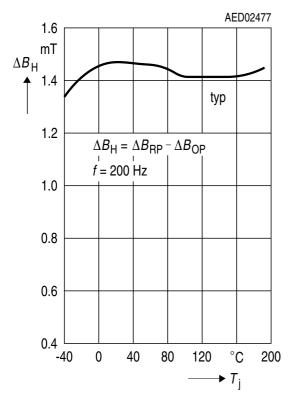


Mean Value of Switching Induction

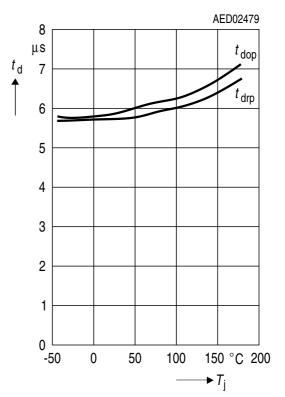




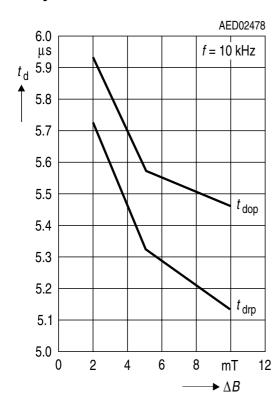
Hysteresis versus Temperature



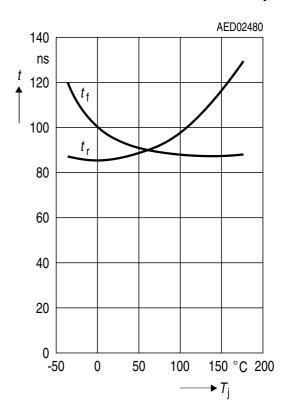
Delay Time 1) versus Temperature



Delay Time 1) versus Differential Field



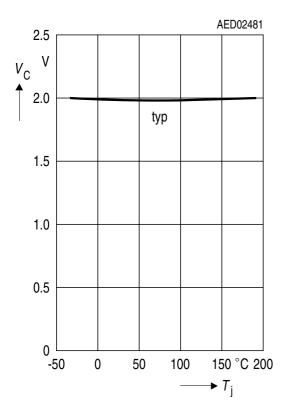
Rise and Fall Time versus Temperature



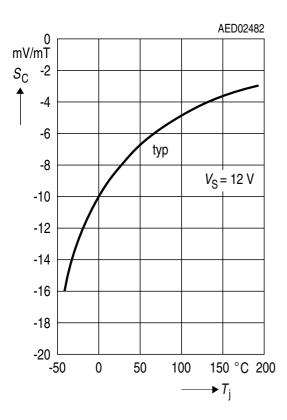
¹⁾ Switching points related to initial measurement @ ΔB = 2 mT, f = 200 Hz



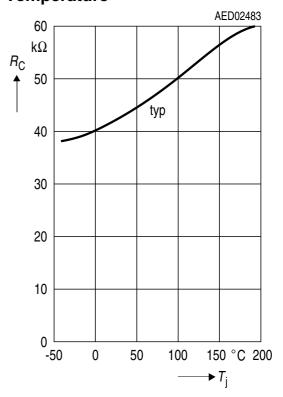
Capacitor Voltage versus Temperature



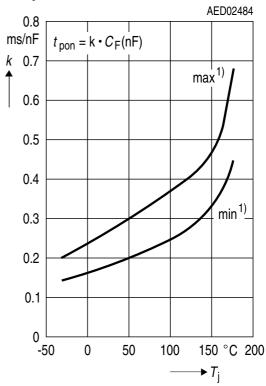
Filter Sensitivity versus Temperature



Filter Input Resistance versus Temperature



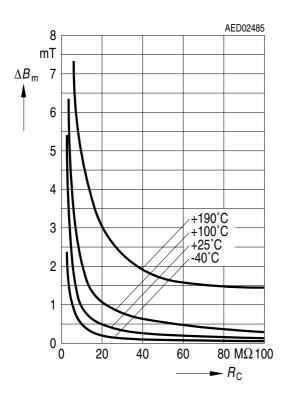
Delay Time $t_{\rm pon}$ for Power ON versus Temperature



 Calculated values for minimum and maximum filter resistance, C_F at room temperature.



Threshold Shift versus Filter Leakage



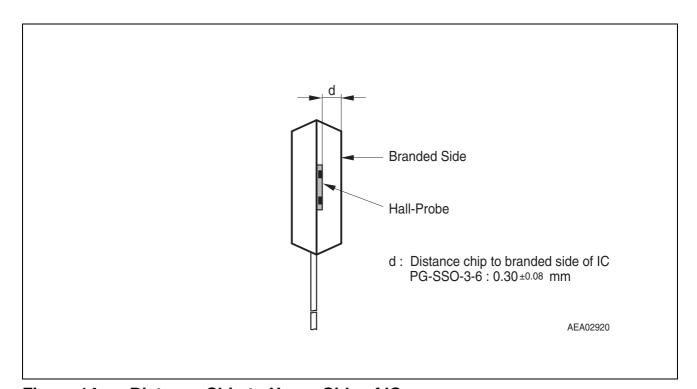


Figure 14 Distance Chip to Upper Side of IC



Package Outlines

8 Package Outlines

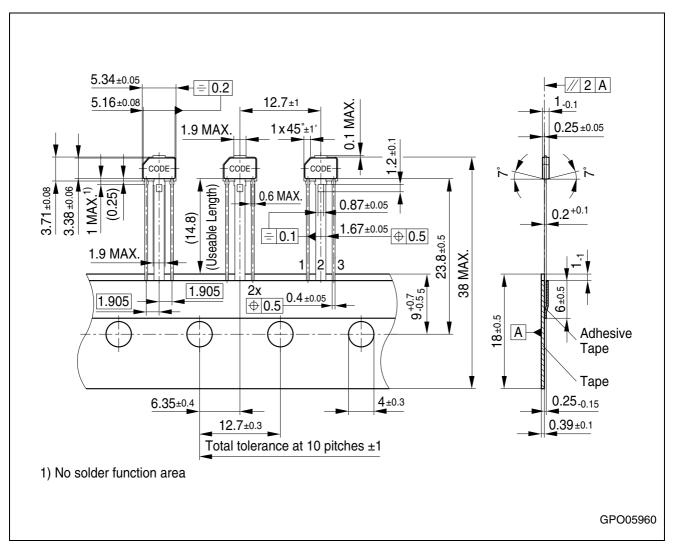


Figure 15 PG-SSO-3-6 (Plastic Single Small Outline Package)

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